

**Listing of Claims**

Claims 1-17 (Cancelled)

18. (Previously Presented) An in-plane switching mode liquid crystal display (LCD) device comprising:

- a gate electrode on a substrate;
- a gate insulating film on an entire surface of the substrate;
- a semiconductor layer and an ohmic contact layer on the gate insulating film;
- a buffer layer on the ohmic contact layer;
- a pixel electrode on the buffer layer;
- source or drain electrodes connected with the pixel electrodes on the buffer layer;
- a passivation layer on the pixel electrode; and
- a common electrode on the passivation layer.

19. (Original) The in-plane switching mode LCD device as claimed in claim 18, wherein the gate electrode includes a low resistance material.

20. (Original) The in-plane switching mode LCD device as claimed in claim 19, wherein the low resistance material includes one of aluminum (Al), copper (Cu), and silver (Ag).

21. (Original) The in-plane switching mode LCD device as claimed in claim 18, wherein the buffer layer includes a metal.

22. (Original) The in-plane switching mode LCD device as claimed in claim 21, wherein the buffer layer includes titanium (Ti).

23. (Original) The in-plane switching mode LCD device as claimed in claim 18, wherein the source and drain electrodes include a low resistance material.

24. (Original) The in-plane switching mode LCD device as claimed in claim 23, wherein the low resistance material includes one of aluminum (Al), copper (Cu), and silver (Ag).

25. (Original) The in-plane switching mode LCD device as claimed in claim 18, wherein the pixel electrode includes transparent conductive material.
26. (Original) The in-plane switching mode LCD device as claimed in claim 25, wherein the pixel electrode includes indium tin oxide.
27. (Original) The in-plane switching mode LCD device as claimed in claim 18, wherein the common electrode includes indium tin oxide.
28. (Currently Amended) A method for manufacturing an in-plane switching mode liquid crystal display (LCD) device comprising:
- forming a gate electrode on a substrate;
  - forming a gate insulating film, a semiconductor layer, an ohmic contact layer, and a buffer layer on the gate electrode;
  - forming a pixel electrode on the buffer layer;
  - forming source and drain electrodes connected with the pixel electrode on the buffer layer;
  - forming a passivation layer on a surface of the substrate; and
  - forming a common electrode on the passivation layer.
29. (Original) The in-plane switching mode LCD device as claimed in claim 28, wherein the gate electrode includes one of aluminum (Al), copper (Cu), and silver (Ag).
30. (Original) The in-plane switching mode LCD device as claimed in claim 28, wherein the buffer layer includes titanium (Ti).
31. (Original) The in-plane switching mode LCD device as claimed in claim 28, wherein the source and drain electrodes include one of aluminum (Al), copper (Cu), and silver (Ag).
32. (Original) The in-plane switching mode LCD device as claimed in claim 28, wherein the pixel electrode includes indium tin oxide.
33. (Original) The in-plane switching mode LCD device as claimed in claim 28, wherein the drain electrode is electrically connected with the pixel electrode.

34. (Original) The in-plane switching mode LCD device as claimed in claim 28, wherein the common electrode includes indium tin oxide.
35. (Original) The in-plane switching mode LCD device as claimed in claim 28, wherein the gate electrode is deposited by a sputtering process.
36. (Original) The in-plane switching mode LCD device as claimed in claim 35, wherein the gate electrode is patterned using photolithography.
37. (Original) The in-plane switching mode LCD device as claimed in claim 28, wherein the semiconductor layer, the ohmic contact layer, and the buffer layer are formed on the gate insulating film by a plasma enhanced chemical vapor deposition (PECVD) process.
38. (Original) The in-plane switching mode LCD device as claimed in claim 37, wherein the semiconductor layer, the ohmic contact layer, and the buffer layer are patterned.
39. (Original) The in-plane switching mode LCD device as claimed in claim 28, wherein the pixel electrode is formed by a sputtering process.
40. (Original) The in-plane switching mode LCD device as claimed in claim 39, wherein the pixel electrode is patterned.
41. (Original) The in-plane switching mode LCD device as claimed in claim 28, wherein the passivation layer is formed by a deposition process.